

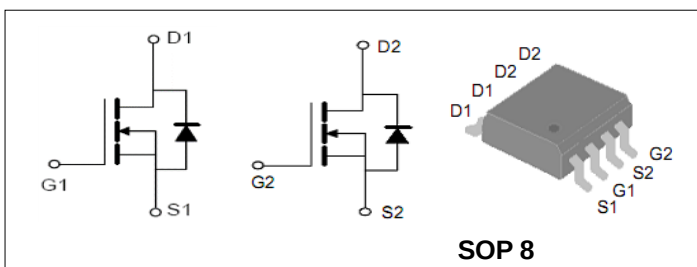
**40V/8A Dual N-Channel Enhancement Mode Power MOSFET****Features**

- Improved dv/dt Capability, High Ruggedness.
- Maximum Junction Temperature Range (150°C)

BVDSS	40	V
ID	8	A
RDSON@VGS=10V	15	mΩ
RDSON@VGS=4.5V	20	mΩ

Applications

- Load switch
- PWM applications

**Order Information**

Product	Package	Marking	Reel Size	Reel	Carton
PTS4008D	SOP-8	PTS4008D	13inch	3000PCS	48000PCS

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{(BR)DSS}	Drain-Source Breakdown Voltage		40	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	TA =25°C	8	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested (Silicon Limit) (Note1)	TA =25°C	32	A
I _D	Continuous Drain current	TA =25°C	8	A
P _D	Maximum Power Dissipation	TA =25°C	2	W
R _{θJA}	Thermal Resistance Junction-to-Ambient (Note2)		62.5	°C/W



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Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
I _{DSS}	Zero Gate Voltage Drain current	VDS=40V,VGS=0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	VDS=VGS,ID=250μA	1	1.6	2.1	V
R _{DS(ON)}	Drain-Source On-State Resistance (Note3)	VGS=10V, ID=7A	--	15	21	mΩ
		VGS=4.5V, ID=6A	--	20	30	
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated) (Note4)						
C _{iss}	Input Capacitance	VDS=20V, VGS=0V, F=1MHz	--	985	--	pF
C _{oss}	Output Capacitance		--	76	--	pF
C _{rss}	Reverse Transfer Capacitance		--	63	--	pF
Q _g	Total Gate Charge	VDS=20V, ID=4A, VGS= 10V	--	15.1	--	nC
Q _{gs}	Gate-Source Charge		--	2.3	--	nC
Q _{gd}	Gate-Drain Charge		--	3.5	--	nC
Switching Characteristics (Note4)						
t _{d(on)}	Turn-on Delay Time	VDS=20V, ID=4A, RG=3Ω, VGS=10V	--	3.6	--	nS
t _r	Turn-on Rise Time		--	9.2	--	nS
t _{d(off)}	Turn-off Delay Time		--	15.9	--	nS
t _f	Turn-off Fall Time		--	7.9	--	nS
Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	ISD=8A,VGS=0V	--	--	1.2	V

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
4. Guranteed by design, not subject to production testing.



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Typical Characteristics

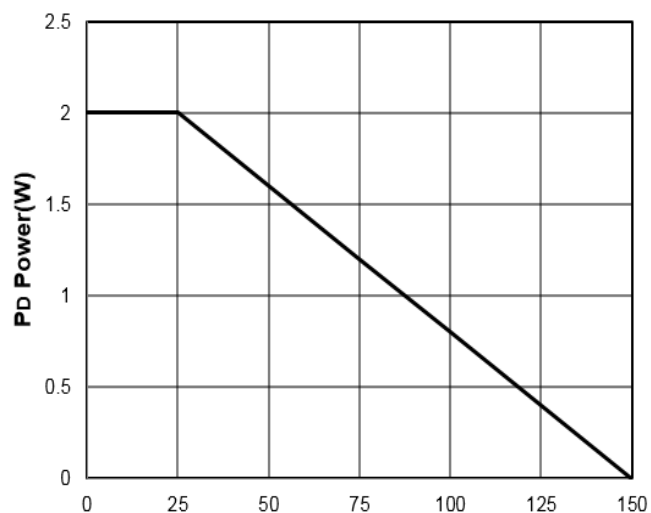


Figure1: T_j -Junction Temperature (°C)

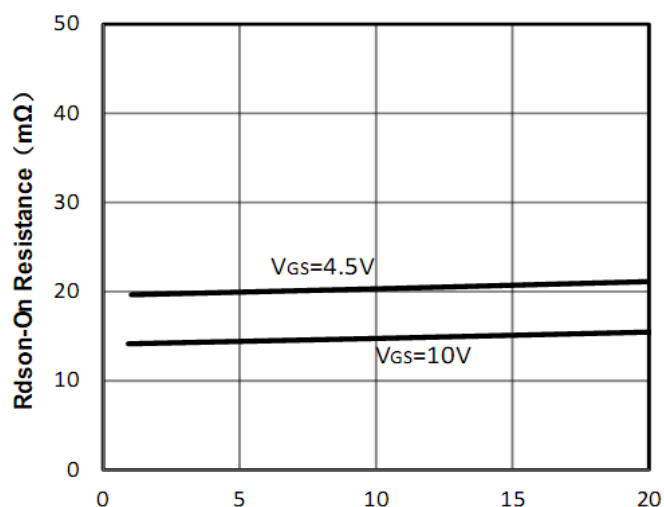


Figure2: I_d -Drain Current (A)

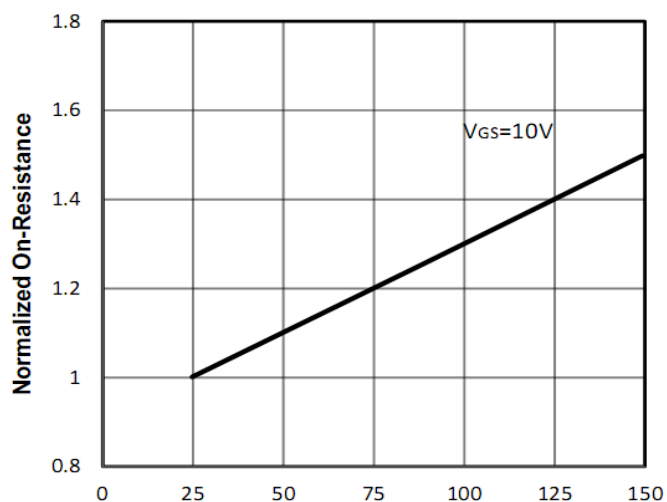


Figure3: T_j -Junction Temperature (°C)

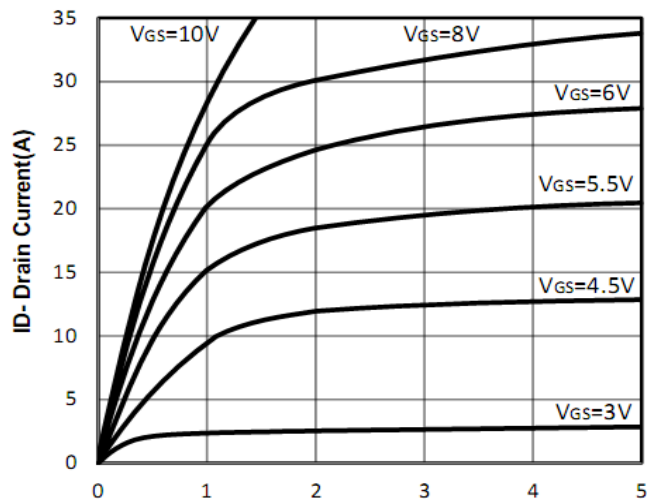


Figure4: V_{ds} -Drain Source Voltage (V)

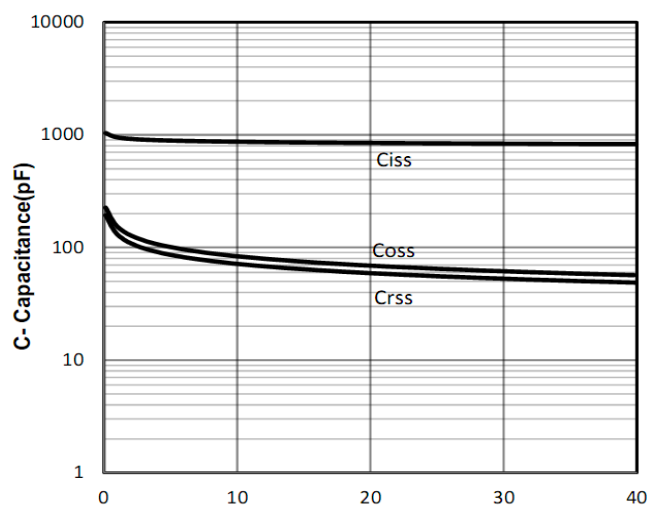


Figure5: V_{ds} -Drain Source Voltage (V)

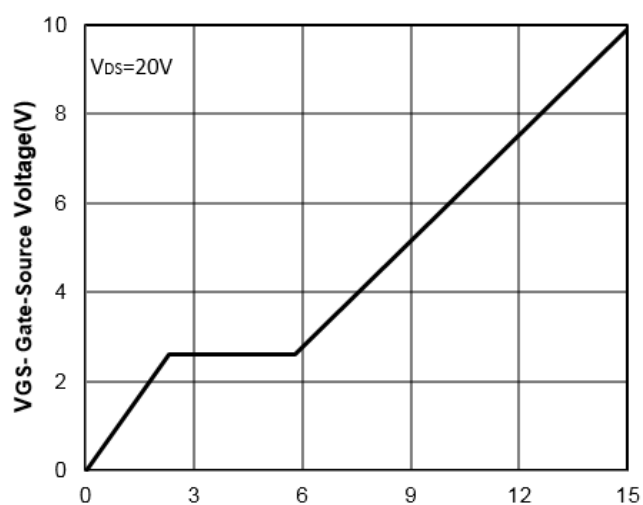


Figure6: Q_g -Gate Charge (nC)



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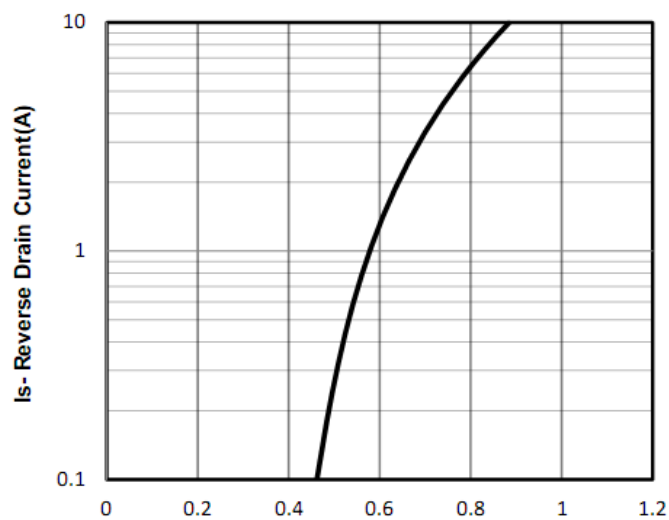


Figure7: Vsd -Source Drain Voltage (V)

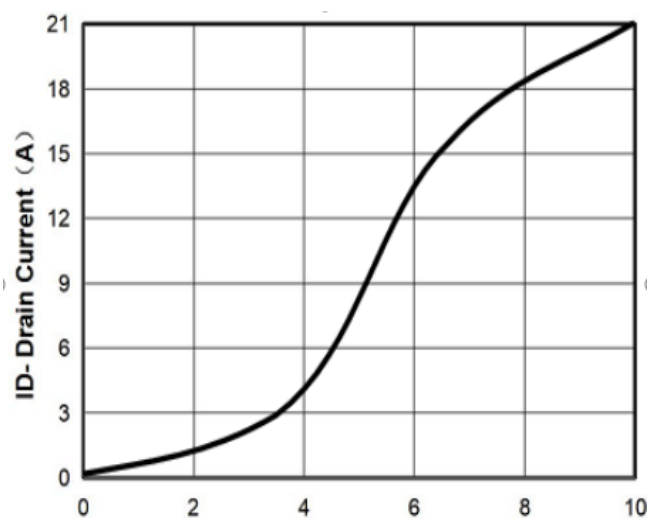


Figure8: Vgs -Gate Source Voltage (V)

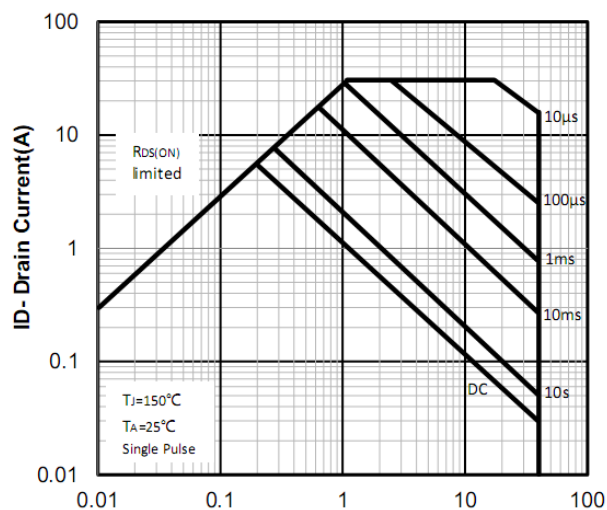


Figure9: Vds -Drain Source Voltage (V)

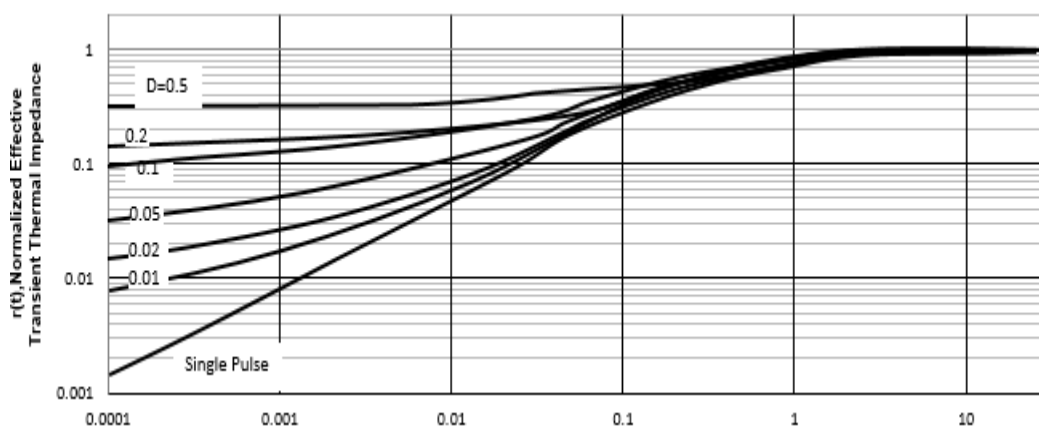
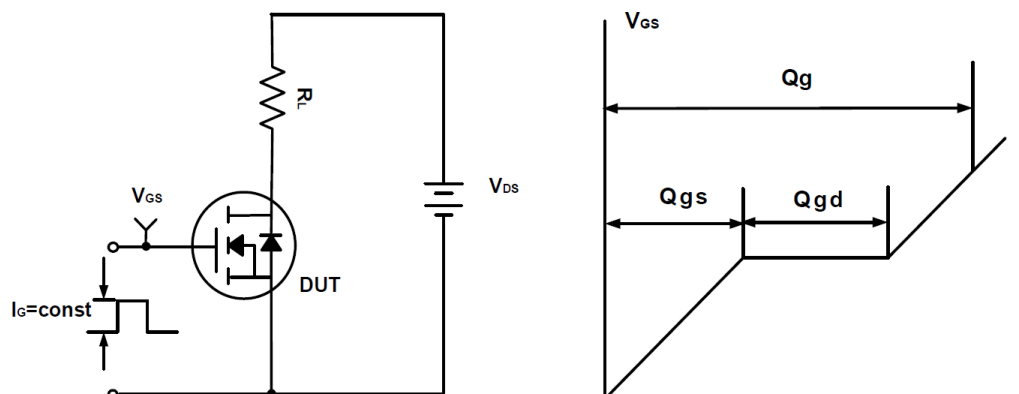
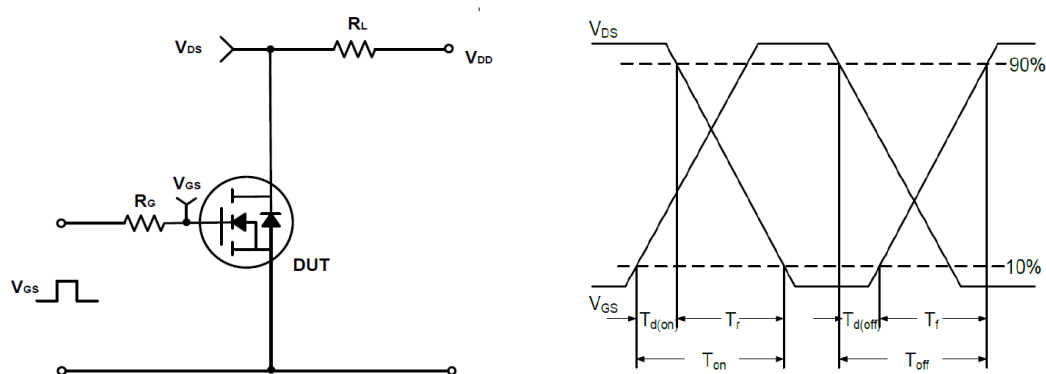
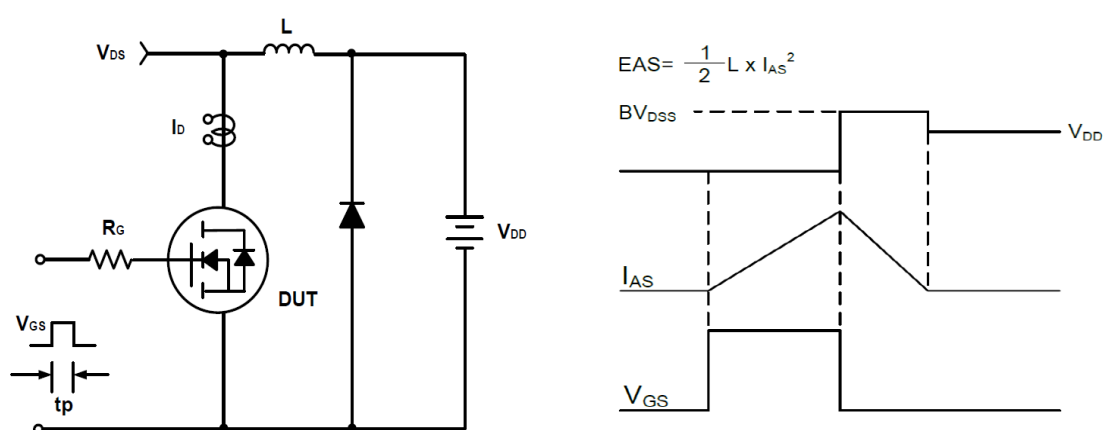


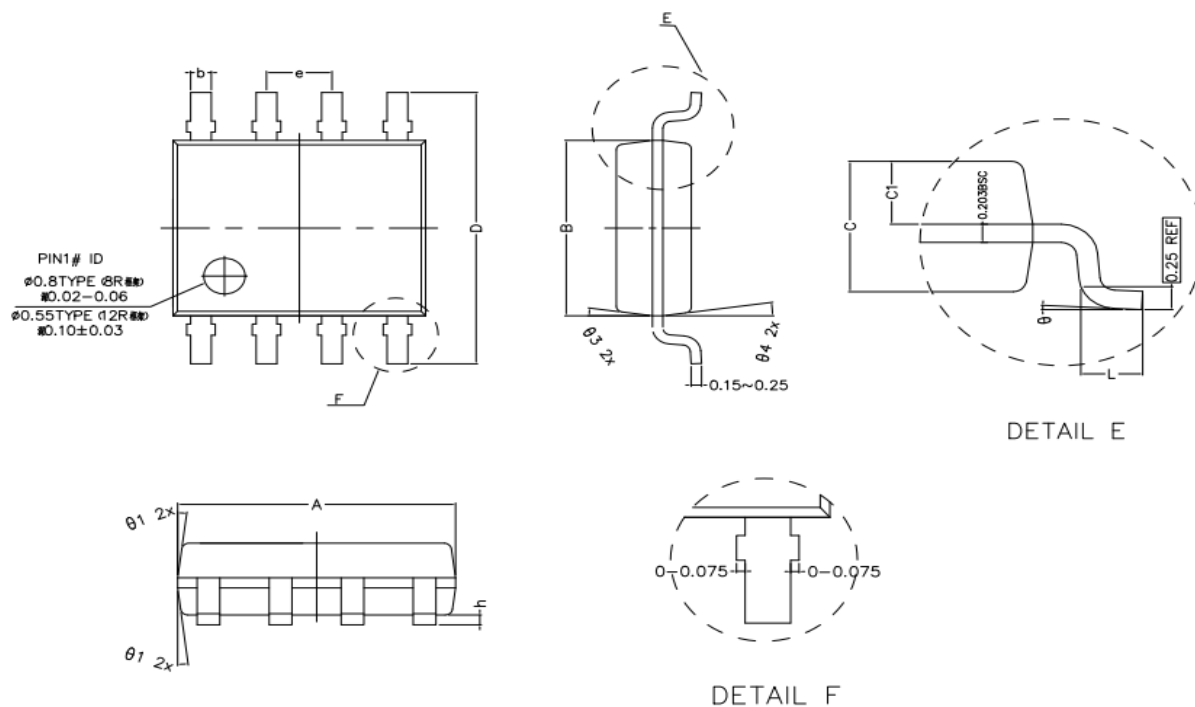
Figure10: Square Wave Pulse Duration (sec)

**40V/8A Dual N-Channel Enhancement Mode Power MOSFET****Test Circuit and Waveform:****Figure A Gate Charge Test Circuit & Waveforms****Figure B Switching Test Circuit & Waveforms****Figure C Unclamped Inductive Switching Circuit & Waveforms**



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SOP-8 Package Outline Dimensions (Units: mm)



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.800	4.900	5.000
B	3.800	3.900	4.000
C	1.350	1.450	1.550
C1	0.650	0.700	0.750
D	5.900	6.100	6.300
L	0.500	0.600	0.700
b	0.350	0.400	0.450
h	0.050	0.150	0.250
e	1.270TYPE		
θ_1	7° TYPE(8R) 12° TYPE(12R)		
θ_2	7° TYPE(8R) 10° TYPE(12R)		
θ_3	8° TYPE(8R) 12° TYPE(12R)		
θ_4	8° TYPE(8R) 10° TYPE(12R)		
θ	0° ~ 8°		